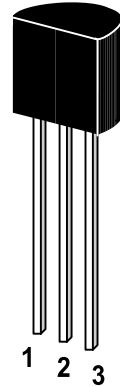


ST 2SC380

NPN Silicon Epitaxial Planar Transistor
High frequency amplifier application

The transistor is subdivided into three groups, R, O,
and Y, according to its DC current gain

On special request, these transistors can be
manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	35	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V_{EBO}	4	V
Collector Current	I_{C}	50	mA
Emitter Current	$-I_{\text{E}}$	50	mA
Power Dissipation	P_{tot}	300	mW
Junction Temperature	T_{j}	125	$^\circ\text{C}$
Storage Temperature Range	T_{s}	-55 to +125	$^\circ\text{C}$

G S P FORM A IS AVAILABLE

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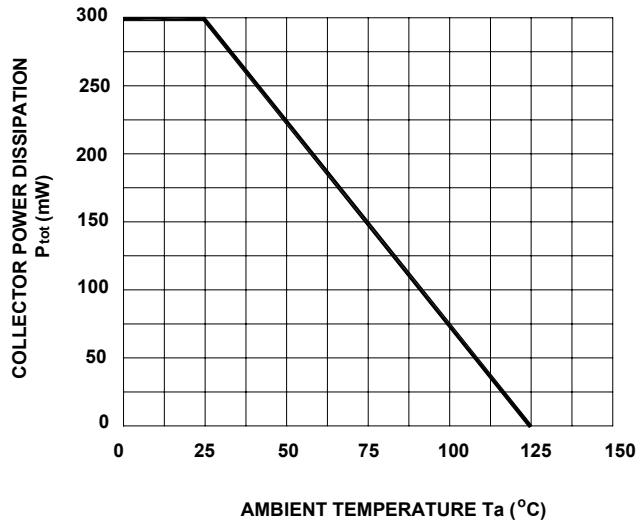
Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE}=12\text{V}$, $I_C=2\text{mA}$					
Current Gain Group R	h_{FE}	40	-	80	-
O	h_{FE}	70	-	140	-
Y	h_{FE}	120	-	240	-
Collector Cutoff Current at $V_{CB}=35\text{V}$	I_{CBO}	-	-	0.1	μA
Emitter Cutoff Current at $V_{EB}=4\text{V}$	I_{EBO}	-	-	0.1	μA
Collector Saturation Voltage at $I_C=10\text{mA}$, $I_B=1\text{mA}$	$V_{CE(sat)}$	-	-	0.4	V
Base Emitter Voltage at $I_C=10\text{mA}$, $I_B=1\text{mA}$	V_{BE}	-	-	1	V
Transition Frequency at $V_{CE}=10\text{V}$, $I_C=1\text{mA}$	f_T	100	-	400	MHz
Collector Output Capacitance at $V_{CB}=10\text{V}$, $f=1\text{MHz}$	C_{ob}	1.4	2.0	3.2	pF
Collector Base Time Constant at $V_{CE}=10\text{V}$, $I_E=-1\text{mA}$, $f=30\text{MHz}$	$C_c, f_{bb'}$	10	-	50	ps
Power Gain at $V_{CC}=6\text{V}$, $f=10.7\text{MHz}$, $I_E=-1\text{mA}$	G_{pe}	27	29	33	dB

G S P FORM A IS AVAILABLE

ST 2SC380

Pc-Ta



hFE-Ic

